# 2SD1138

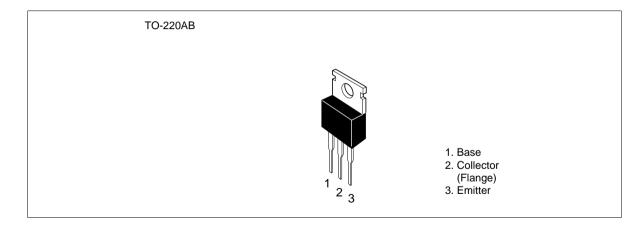
## Silicon NPN Triple Diffused

# **HITACHI**

### **Application**

Low frequency high voltage power amplifier TV vertical deflection output complementary pair with 2SB861

### Outline





## **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Rating	Unit
Collector to base voltage	V <sub>CBO</sub>	200	V
Collector to emitter voltage	V <sub>CEO</sub>	150	V
Emitter to base voltage	$V_{EBO}$	6	V
Collector current	I <sub>c</sub>	2	A
Collector peak current	I <sub>C (peak)</sub>	5	A
Collector power dissipation	P <sub>c</sub>	1.8	W
	P <sub>c</sub> * <sup>1</sup>	30	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-45 to +150	°C

Note: 1. Value at  $T_c = 25^{\circ}C$ .

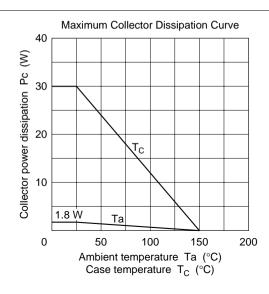
## **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

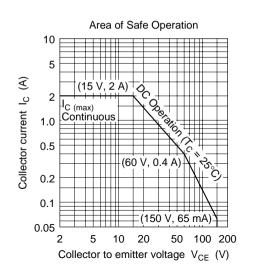
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	150	_	_	V	$I_{\text{C}}$ = 50 mA, $R_{\text{BE}}$ = $\infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	_	_	V	$I_{\rm E} = 5 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	1	μΑ	V <sub>CB</sub> = 120 V, I <sub>E</sub> = 0
DC current transfer ratio	h <sub>FE1</sub> *1	60	_	320		$V_{CE} = 4 \text{ V}, I_{C} = 50 \text{ mA}$
	h <sub>FE2</sub>	60	_	_		$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE (sat)}}$	_	_	3.0	V	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}^{*2}$
Base to emitter voltage	$V_{BE}$	_	_	1.0	V	$V_{CB} = 4 \text{ V}, I_{C} = 50 \text{ mA}$
Collector output capacitance	Cob	_	20	_	pF	$V_{CB} = 100 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

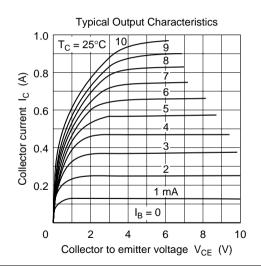
Note: 1. The 2SD1138 is grouped by  $h_{FE1}$  as follows.

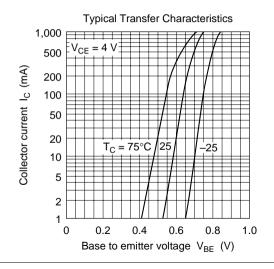
2. Pulse test.

В	С	D	
60 to 120	100 to 200	160 to 320	

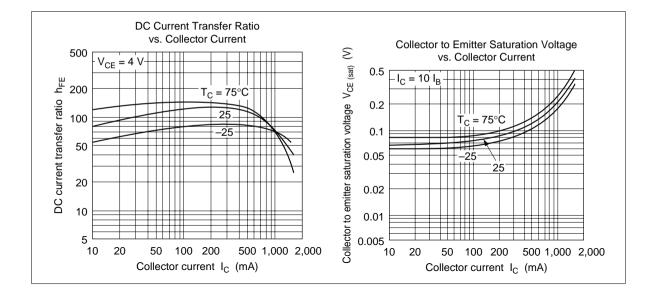




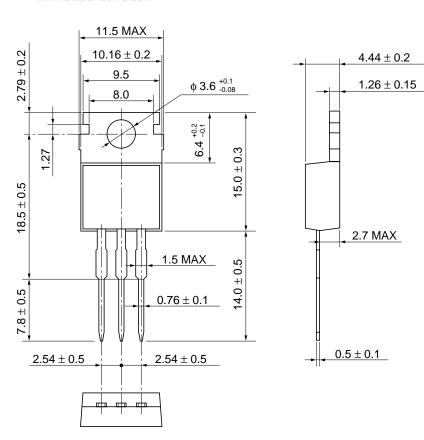


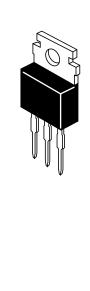


## 2SD1138



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Hitachi Code	1310-220MB 1111
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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# HITACHI

#### Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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#### For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park

Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000

Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Lower Cookham Road

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180 Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218

Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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